BT150NP170EF

General Description

BT150NP170EF IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as 3-level-applications.



Features

- Low VCE(sat) trench IGBT technology
- Low switching loss
- 10μs short circuit capability
- Low inductance case
- VCE(sat) with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper base plate using DBC technology

Applications

- Solar power
- UPS
- 3-level applications

Parameters

Type	V_{CE}	I_C	T_{vjmax}
BT150NP170EF	1700V	150A	175°C

CONFIDE